AMENDMENTS TO THE CLAIMS

1. (Original) A substrate plating apparatus for plating a substrate, comprising:

a plating unit including at least one plating chamber for containing a plating solution for plating a metal layer onto a semiconductor substrate;

a concentration analyzing device to analyze concentrations of the plating solution, wherein said concentration analyzing device includes a metal ion concentration analyzer and a plating additive concentration analyzer; and

a plating solution preparing unit for preparing the plating solution based on results from said concentration analyzing device.

2. (New) A method of processing a semiconductor substrate in a processing system segmented into a wet area and a dry area, the method comprising:

introducing said semiconductor substrate into said dry area of said processing system;

moving said semiconductor substrate into said wet area of said processing system;

processing said semiconductor substrate in a plating chamber disposed within said wet area;

cleaning and drying said semiconductor substrate in a cleaning and drying unit disposed between said wet area and said dry area; and

transferring said semiconductor substrate to said dry area of said processing system.

3. (New) The method of claim 2, wherein cleaning and drying said semiconductor substrate comprises:

spinning said semiconductor substrate at a high angular velocity.

4. (New) The method of claim 2, wherein processing said semiconductor substrate in said plating chamber comprises immersing said semiconductor substrate in a plating solution contained in said plating chamber.

5. (New) A method of processing a semiconductor substrate in a processing system segmented into a wet area and a dry area, the method comprising:

introducing said semiconductor substrate into said dry area of said processing system;

moving said semiconductor substrate into said wet area of said processing system;

processing said semiconductor substrate in an electrochemical process cell disposed within said wet area;

cleaning and drying said semiconductor substrate using a spin-dry system disposed between said wet area and said dry area, wherein cleaning said semiconductor substrate comprises spinning and rinsing said semiconductor substrate; and

transferring said semiconductor substrate to said dry area of said processing system.